

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-100V	70m Ω @-10V	-22A
	85m Ω @-4.5V	

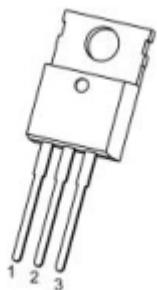
Feature

- Advanced trench process technology
- Super high dense cell design

Application

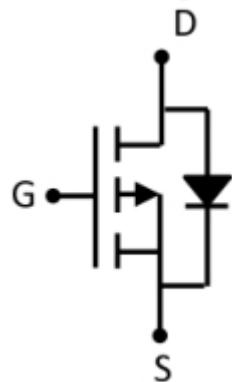
- Motor control
- Power management
- DC/DC convertor

Package

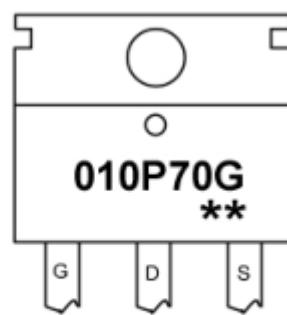


TO-220-3L-C(1:G 2:D 3:S)

Circuit diagram



Marking



010P70G =Device Code

****** =Week Code

Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

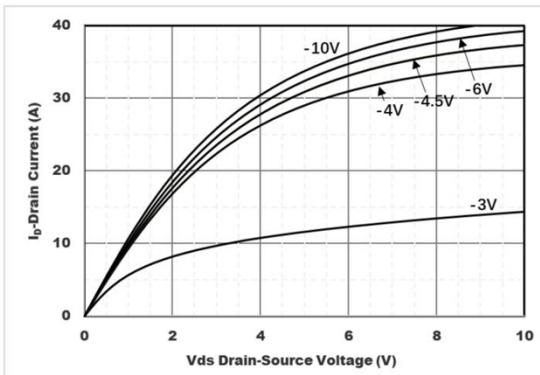
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous ($T_c=25^\circ\text{C}$)	I_D	-22	W
Drain Current – Pulsed	I_{DM}	-88	A
Power Dissipation ($T_c=25^\circ\text{C}$)	P_D	90	W
Thermal Resistance Junction to Case	$R_{\theta JC}$	1.38	$^\circ\text{C} / \text{W}$
Storage Temperature Range	T_{STG}	-55 ~ +150	$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55 ~ +150	$^\circ\text{C}$

Electrical characteristics

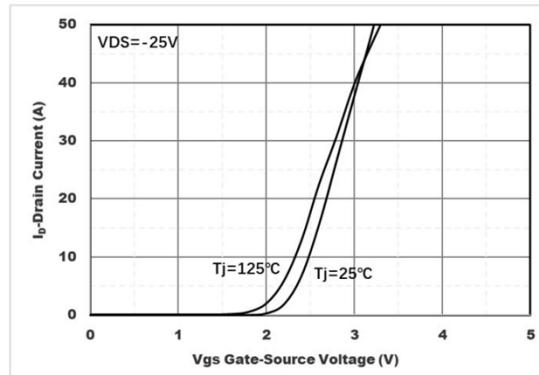
($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = -250\mu\text{A}$	-100			V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}} = -100\text{V}, V_{\text{GS}} = 0\text{V}$			-1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}} = \pm 20\text{V}, V_{\text{DS}} = 0\text{V}$			± 100	μA
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = -250\mu\text{A}$	-1	-1.7	-2.5	V
Static Drain-Source on-Resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}} = -10\text{V}, I_{\text{D}} = -10\text{A}$		70	88	$\text{m}\Omega$
		$V_{\text{GS}} = -4.5\text{V}, I_{\text{D}} = -5\text{A}$		85	115	
Dynamic characteristics⁴						
Input Capacitance	C_{iss}	$V_{\text{DS}} = -50\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		1050		pF
Output Capacitance	C_{oss}			120		
Reverse Transfer Capacitance	C_{rss}			23		
Total Gate Charge	Q_g	$V_{\text{GS}} = -10\text{V}, V_{\text{DS}} = -50\text{V}, I_{\text{D}} = -10\text{A}$		20		nC
Gate-Source Charge	Q_{gs}			4		
Gate-Drain Charge	Q_{gd}			4.4		
Turn-On Delay Time	$T_{\text{d(on)}}$	$V_{\text{GS}} = -10\text{V}, V_{\text{DD}} = -50\text{V}, I_{\text{D}} = -10\text{A}, R_{\text{GEN}} = 9.1\Omega$		15		nS
Rise Time	T_r			30		
Turn-Off Delay Time	$T_{\text{d(off)}}$			73		
Fall Time	T_f			76		
Drain-Source Diode Characteristics						
Diode forward voltage	V_{SD}	$V_{\text{GS}} = 0\text{V}, I_s = -1\text{A}$			-1.2	V

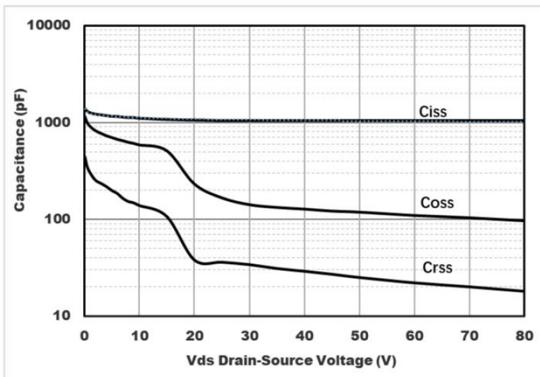
Typical Characteristics



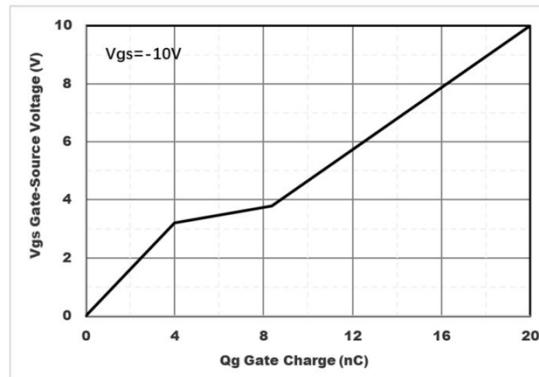
Output Characteristics



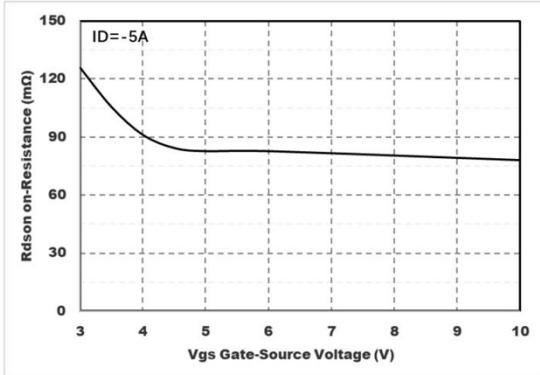
Transfer Characteristics



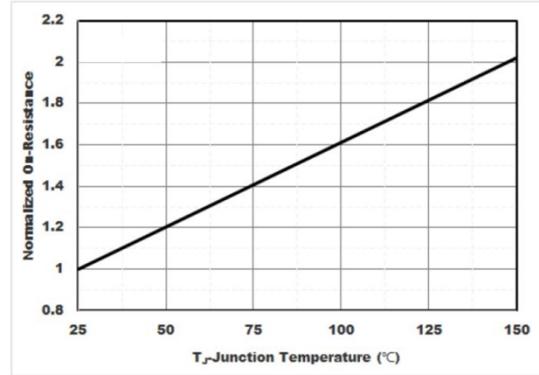
Capacitance Characteristics



Gate Charge



On-Resistance vs. Gate to Source Voltage

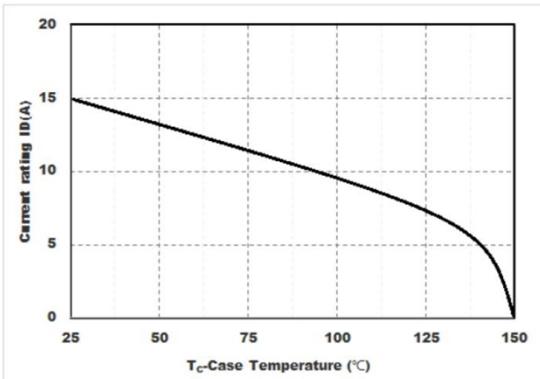


Normalized On-Resistance

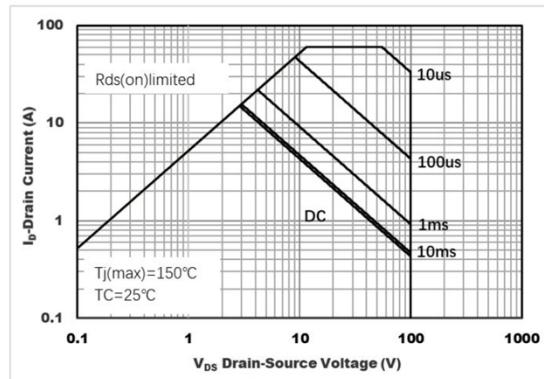


ZL MOSFET

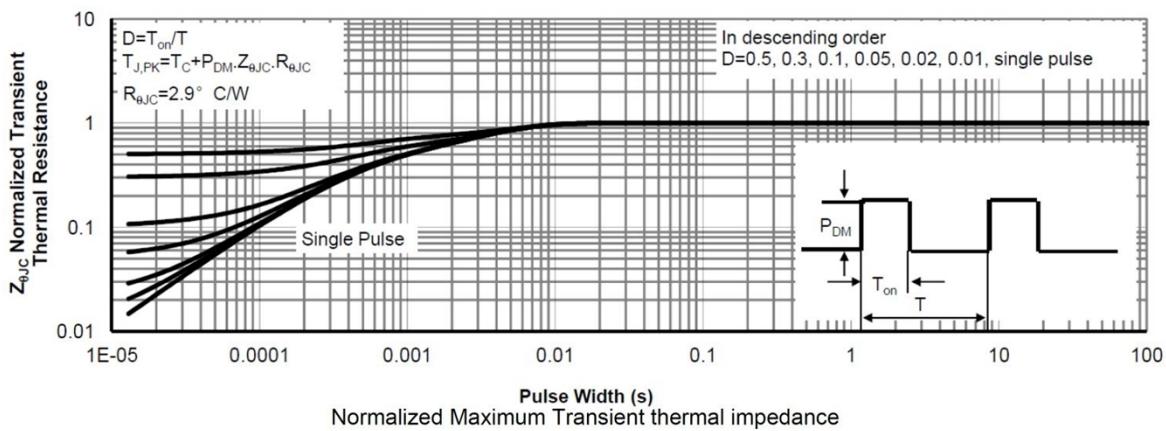
ZL010P70GB



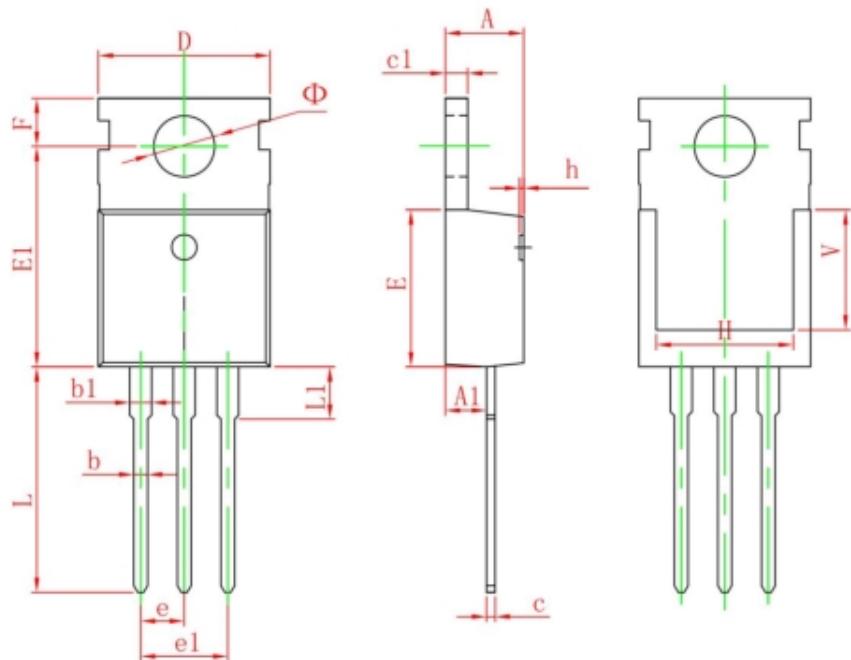
Drain current



Safe Operation Area



TO-220-3L-C Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	13.050	0.498	0.514
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276 REF.	
Φ	3.400	3.800	0.134	0.150